



ACE7407A

P-Channel Enhancement Mode MOSFET

Description

The ACE7407A is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density, DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other battery powered circuits where high-side switching, and low in-line power loss are needed in a very small outline surface mount package.

Features

- -20V/-3.4A, $R_{DS(ON)} = 100m\Omega @ VGS = -4.5V$
- -20V/-2.4A, $R_{DS(ON)} = 125m\Omega @ VGS = -2.5V$
- -20V/-1.7A, $R_{DS(ON)} = 150m\Omega @ VGS = -1.8V$
- -20V/-1.0A, $R_{DS(ON)} = 220m\Omega @ VGS = -1.25V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability

Application

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter



ACE7407A

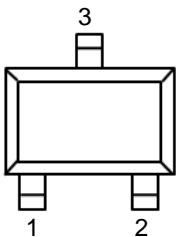
P-Channel Enhancement Mode MOSFET

Absolute Maximum Ratings

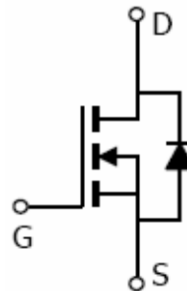
Parameter	Symbol	Max	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GSS}	± 12	V
Continuous Drain Current ($T_J=150^\circ\text{C}$)	I_D	$T_A=25^\circ\text{C}$	-2.3
		$T_A=70^\circ\text{C}$	-1.7
Pulsed Drain Current	I_{DM}	-6	A
Continuous Source Current (Diode Conduction)	I_S	-1.4	A
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	0.33
		$T_A=70^\circ\text{C}$	0.21
Operating Junction Temperature	T_J	-55/150	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55/150	$^\circ\text{C}$
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	105	$^\circ\text{C/W}$

Packaging Type

SOT-323

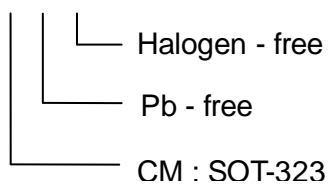


SOT-323	Description
1	Gate
2	Source
3	Drain



Ordering information

ACE7407A CM + H





ACE7407A

P-Channel Enhancement Mode MOSFET

Electrical Characteristics

$T_A=25^{\circ}\text{C}$, unless otherwise noted

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.35		-0.8	
Gate Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 12V$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=-20V, V_{GS}=0V$			-1	uA
		$V_{DS}=-20V, V_{GS}=0V, T_J=55^{\circ}\text{C}$			-5	
		$V_{DS}\geq -5V, V_{GS}=-4.5V$	-6			A
Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=-4.5V, I_D=-3.4A$		0.080	0.100	Ω
		$V_{GS}=-2.5V, I_D=-2.4A$		0.105	0.125	
		$V_{GS}=-1.8V, I_D=-1.7A$		0.130	0.150	
		$V_{GS}=-1.25V, I_D=-1.0A$		0.180	0.22	
Forward Transconductance	Gfs	$V_{DS}=-5V, I_D=-2.8A$		6		S
Diode Forward Voltage	V_{SD}	$I_S=-1.5A, V_{GS}=0V$		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	$V_{DS}=-6V, V_{GS}=-4.5V, I_D=-2.8A$		4.8	8	nC
Gate-Source Charge	Q_{gs}			1.0		
Gate-Drain Charge	Q_{gd}			1.0		
Input Capacitance	C_{iss}	$V_{DS}=-6V, V_{GS}=0V, f=1\text{MHz}$		485		pF
Output Capacitance	C_{oss}			85		
Reverse Transfer Capacitance	C_{rss}			40		
Turn-On Time	td(on)	$V_{DD}=-6V, R_L=6\Omega, V_{GEN}=-4.5V, I_D=-1.0A, R_G=6\Omega$		10	16	nS
	tr			13	23	
Turn-Off Time	td(off)			18	25	
	tf			15	20	

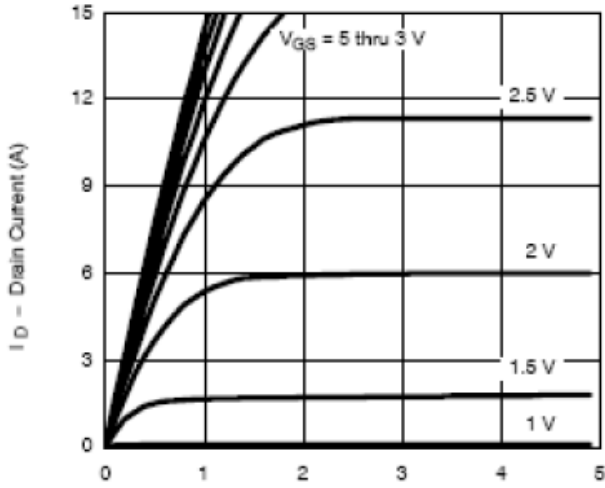


ACE7407A

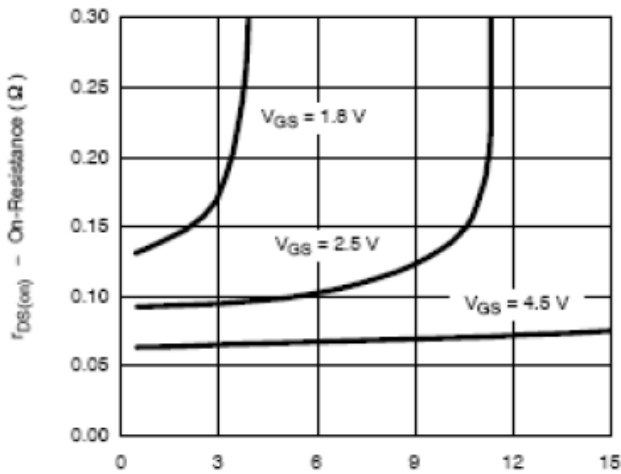
P-Channel Enhancement Mode MOSFET

Typical Performance Characteristics

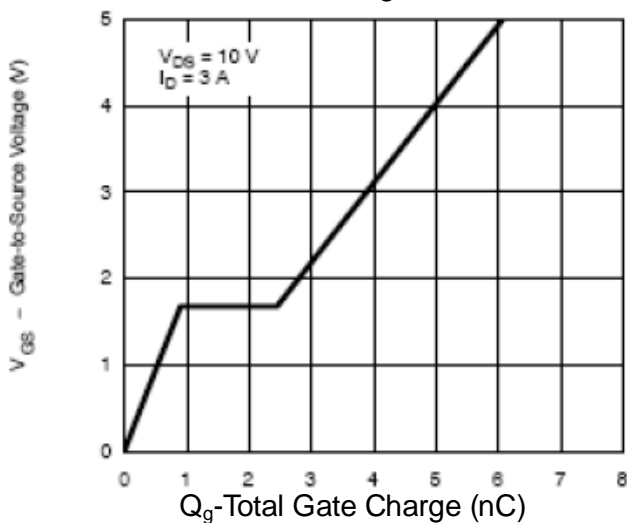
Output Characteristics



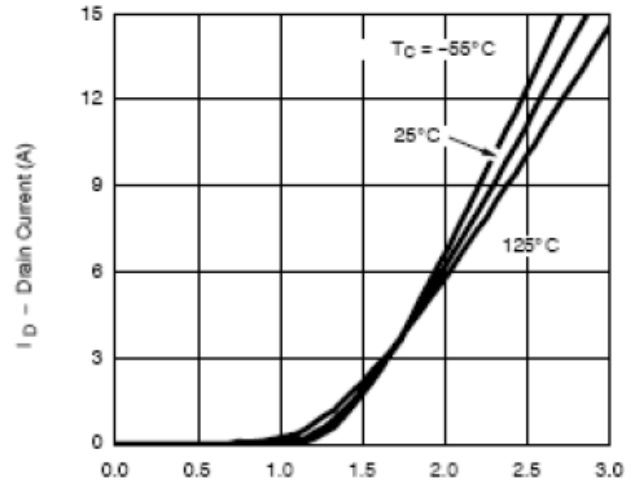
On-Resistance vs. Drain Current



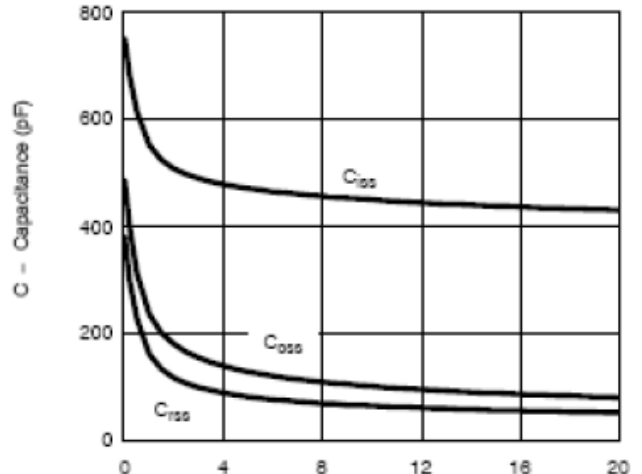
Gate Charge



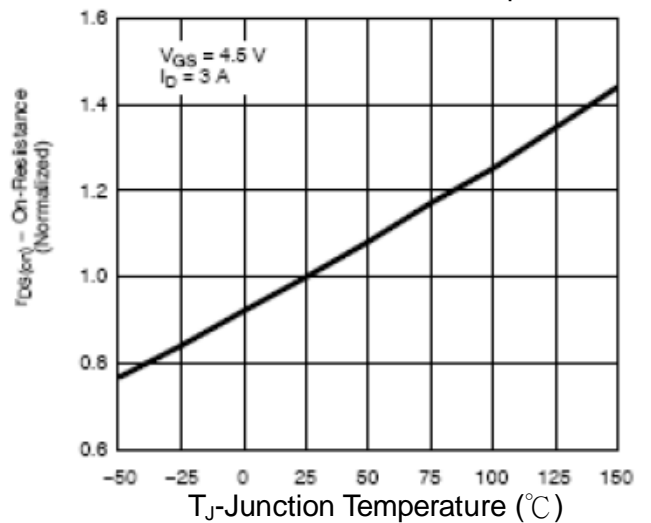
Transfer Characteristics



Capacitance



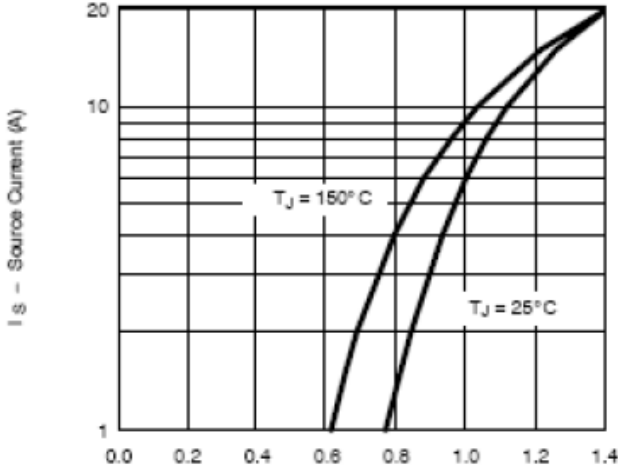
On-Resistance vs. Junction Temperature



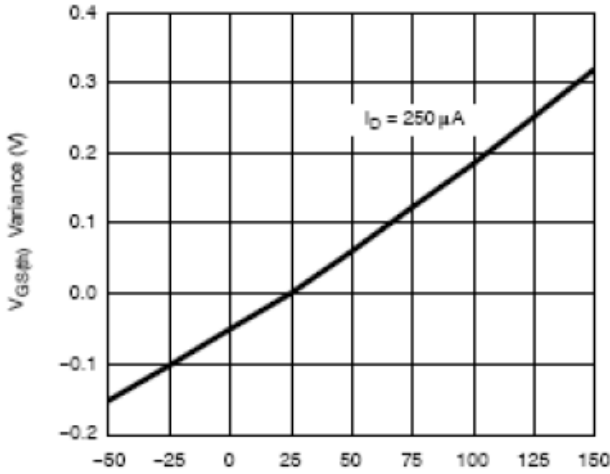


Typical Performance Characteristics

Source-Drain Diode Forward Voltage

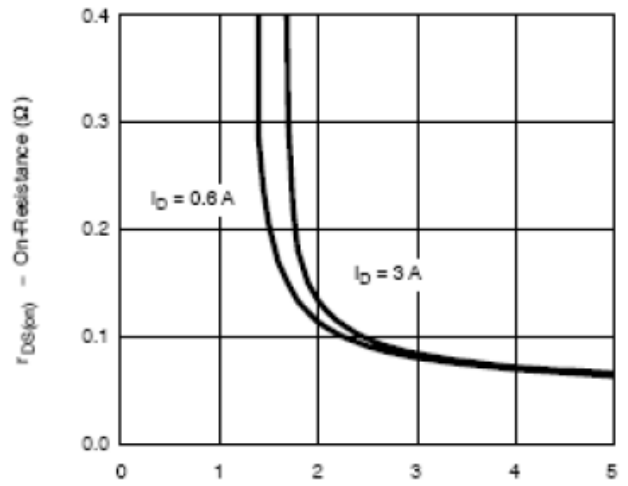


Threshold Voltage



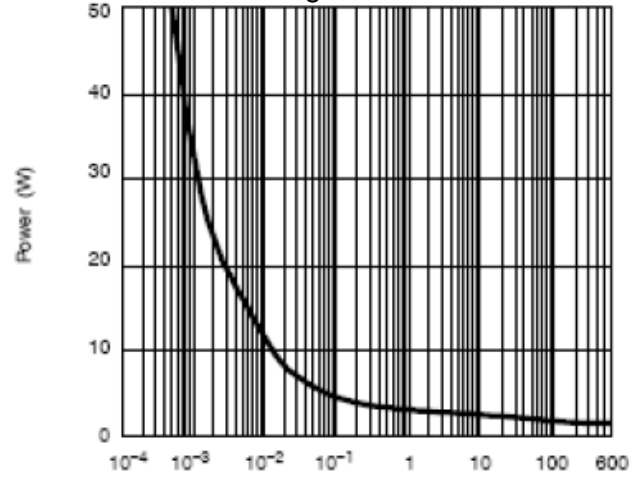
T_J -Temperature($^\circ\text{C}$)

On-Resistance vs. Gate-to-Source Voltage



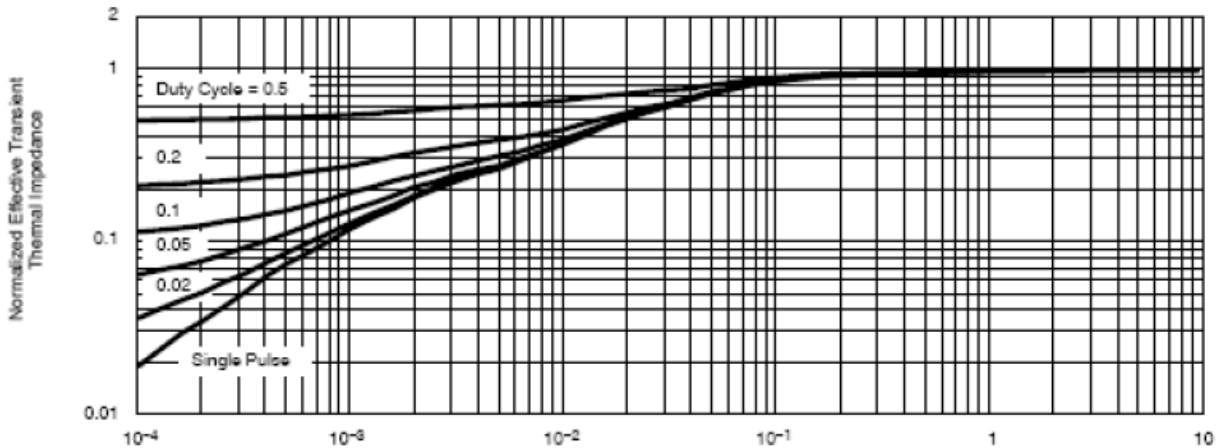
V_{GS} -Gate-to-Source Voltage (V)

Single Pulse Power



Time (sec)

Normalized Thermal Transient Impedance, Junction-to Foot



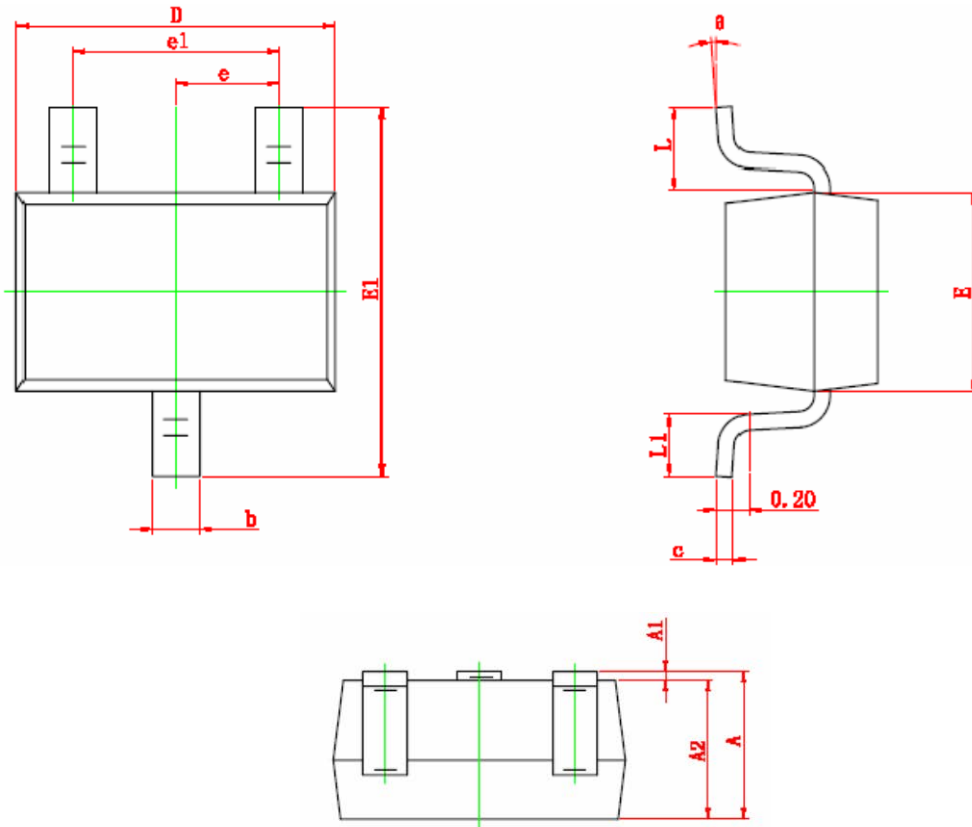
Square Wave Pulse Duration (sec)



ACE7407A P-Channel Enhancement Mode MOSFET

Packing Information

SOT-323



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°



ACE7407A

P-Channel Enhancement Mode MOSFET

Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ACE Technology Co., LTD.
<http://www.ace-ele.com/>